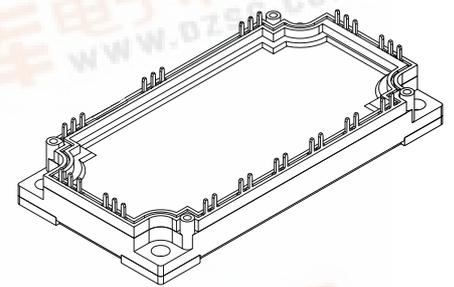
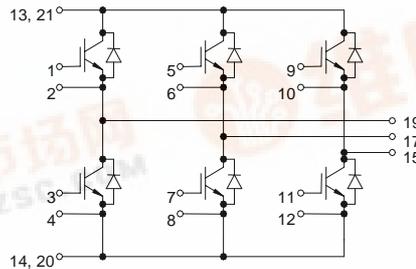


IGBT Modules

Sixpack

Short Circuit SOA Capability
Square RBSOA

$I_{C25} = 130 \text{ A}$
 $V_{CES} = 1200 \text{ V}$
 $V_{CE(sat) \text{ typ.}} = 2.0 \text{ V}$



IGBTs			
Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	1200	V
V_{GES}		± 20	V
I_{C25}	$T_C = 25^{\circ}\text{C}$	130	A
I_{C80}	$T_C = 80^{\circ}\text{C}$	90	A
RBSOA	$V_{GE} = \pm 15 \text{ V}; R_G = 15 \Omega; T_{VJ} = 125^{\circ}\text{C}$ Clamped inductive load; $L = 100 \mu\text{H}$	$I_{CM} = 150$ $V_{CEK} \leq V_{CES}$	A
t_{SC} (SCSOA)	$V_{CE} = 900 \text{ V}; V_{GE} = \pm 15 \text{ V}; R_G = 15 \Omega; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	μs
P_{tot}	$T_C = 25^{\circ}\text{C}$	500	W

Features

- IGBTs
 - low saturation voltage
 - positive temperature coefficient
 - fast switching
 - short tail current for optimized performance also in resonant circuits
- HiPerFRED™ diode:
 - fast reverse recovery
 - low operating forward voltage
 - low leakage current
- Industry Standard Package
 - solderable pins for PCB mounting
 - isolated copper base plate

Typical Applications

- AC drives
- power supplies with power factor correction

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 75 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		2.0 2.2	V V
$V_{GE(th)}$	$I_C = 3 \text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		1.1	1.1 mA mA
I_{GES}	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			400 nA
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 600 \text{ V}; I_C = 75 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 15 \Omega$		150	ns
			60	ns
			680	ns
			50	ns
			9.0	mJ
			7.5	mJ
C_{ies}	$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$		5.7	nF
Q_{Gon}	$V_{CE} = 600 \text{ V}; V_{GE} = 15 \text{ V}; I_C = 75 \text{ A}$		0.75	μC
R_{thJC}	(per IGBT)			0.25 K/W

